

**EXHIBIT LIST: *INTER PARTES* REVIEW OF U.S.  
PATENT NO. 6,563,133**

- TSMC1001: U.S. Patent No. 6,563,133 B1 to Tong Filed: August 9, 2000, Issued: May 13, 2003 (“133 Patent”)
- TSMC1002: File Wrapper of U.S. Patent No. 6,563,133 B1 to Tong, Application No. 09/635,272, filed August 9, 2000
- TSMC1003: Declaration of Dr. Richard A. Blanchard in Support of Petition for *Inter Partes* Review of U.S. Patent No. 6,563,133
- TSMC1004: Thomson Reuters Expert Witness Services Consultant Curriculum Vitae: Richard A. Blanchard, Ph.D.
- TSMC1005: U.S. Patent No. 6,534,381 to Cheung et al., Filed: January 4, 2000, Issued: March 18, 2003 (“Cheung”)
- TSMC1006: U.S. Patent No. 5,561,072 to Saito, Filed: November 21, 1994, Issued: October 1, 1996 (“Saito”)
- TSMC1007: Seiji Fujino et al., Silicon Wafer Direct Bonding through the Amorphous Layer, 34 Japanese J. Appl. Phys. 1322 (15 October 1995) (“Fujino”)
- TSMC1008: Shiyang Tian et al., A Detailed Physical Model for Ion Implant Induced Damage in Silicon, 45 (6) IEEE Transactions on Electron Devices 1226 (June 1998) (“Tian”)
- TSMC1009: RANDOM HOUSE WEBSTER’S COLLEGE DICTIONARY 884 (Random House, Inc. 2000) (1991)